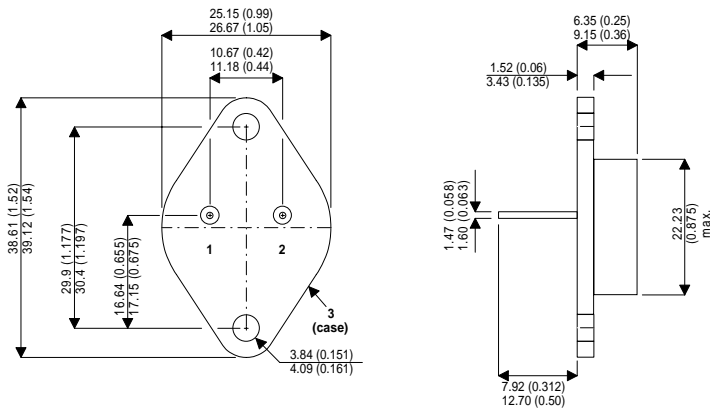


MECHANICAL DATA

Dimensions in mm(inches)

NPN SILICON POWER TRANSISTOR



FEATURES

- HIGH CURRENT
- FAST SWITCHING
- HIGH RELIABILITY

APPLICATIONS

- POWER SWITCHING CIRCUITS
- MOTOR CONTROL

TO-204AE (TO-3)

PIN 1 — Base PIN 2 — Emitter Case is Collector.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage ($I_E = 0$)	500V
V_{CEX}	Collector – Emitter Voltage ($V_{BE} = -1.5V$)	500V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	500V
V_{CER}	Collector – Emitter Voltage ($R_{BE} = 100\Omega$)	500V
V_{EBO}	Emitter – Base Voltage ($I_C = 0$)	7V
I_C	Collector Current	15A
I_{CM}	Peak Collector Current ($t_p = 10$ ms)	20A
I_B	Base Current	3A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25^{\circ}C$	350W
T_{stg}	Storage Temperature	-65 to 200°C
T_j	Junction Temperature	200°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	0.5°C/W

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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CEO(BR)^*}$	Collector - Emitter Breakdown Voltage $I_C = 200mA$	500			V
V_{EBO}	Emitter – Base Voltage $I_E = 50mA$ $I_C = 0$	7			V
I_{CEO}	Collector Cut-off Current $V_{CE} = 400V$ $I_B = 0$			3	mA
I_{CEX}	Collector Cut-off Current $V_{CE} = 500V$ $V_{BE} = -1.5V$ $T_C = 125^{\circ}C$			3 12	mA
I_{EBO}	Emitter Cut-off Current $I_C = 0$ $V_{EB} = 5V$			1.0	mA
$V_{CE(sat)^*}$	Collector – Emitter Saturation Voltage $I_C = 4A$ $I_B = 0.8A$		0.2	0.6	V
	$I_C = 8A$ $I_B = 1.6A$		0.6	1.0	
$V_{BE(sat)^*}$	Base – Emitter Saturation Voltage $I_C = 8A$ $I_B = 1.6A$		1.2	1.5	V
h_{FE}^*	DC Current Gain $V_{CE} = 4V$ $I_C = 4A$		15	60	—
	$V_{CE} = 4V$ $I_C = 8A$		8		
$I_{S/b}$	Second Breakdown Collector Current $V_{CE} = 140V$ $t = 1s$		0.15		A
	$V_{CE} = 25V$ $t = 1s$		14		
f_T	Transition Frequency $I_C = 2A$ $V_{CE} = 15V$ $f = 10MHz$		8		MHz
t_{on}	Turn-On Time $I_C = 8A$ $I_{B1} = 1.6A$			0.9	μs
t_s	Storage Time $I_C = 8A$ $I_{B1} = 1.6A$ $I_{B2} = -1.6A$			3.5	
t_f	Fall Time $I_C = 8A$ $I_{B1} = 1.6A$ $I_{B2} = -1.6A$			0.9	

(*) Pulse test: $t_p \leq 300\mu s$, $\delta \leq 2\%$

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